

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application.

LISTING OF CLAIMS:

- 1.-9. (Cancelled)
10. (Currently amended) A semiconductor component comprising:
 - at least one first vertical power component extending from a front side to a back side of a silicon substrate; and
 - at least one lateral, active component between which at least one trench filled with an insulation is placed, said at least one trench extending from said front side to said back side of said silicon substrate,
 - wherein said insulation comprises at least partly one dielectric~~and~~,
 - wherein said at least one vertical power component and said at least one lateral, active component are designed approximately ring-shaped and/or disk-shaped and are arranged eccentrically or concentrically around a common point of reference on said silicon substrate, and
 - wherein said at least one trench extends substantially along an entire depth of said at least one first vertical power component.
11. (Previously presented) A semiconductor component according to claim 10, wherein said at least one power component is an IGBT, a PMOS and/or a diode.
12. (Previously presented) A semiconductor component according to claim 10, wherein said at least one power component is suited for voltages of up to 1700 V.
13. (Previously presented) A semiconductor component according to claim 10, wherein said insulation is composed of a combination of insulating, semiconducting and/or conducting materials.

14. (Previously presented) A semiconductor component according to claim 10, wherein said insulation is composed of a combination of a dielectric and polysilicon.
15. (Previously presented) A semiconductor component according to claim 10, wherein said first vertical power component and/or said at least one lateral, active component is completely encompassed by at least one filled trench and/or said at least one second vertical power component.
16. (Previously presented) A semiconductor component according to claim 10, wherein said at least one lateral, active component is placed in a doped trough.
17. (Previously presented) A semiconductor component according to claim 10, wherein a dielectric is applied on said back side of said substrate.
18. (Previously presented) A semiconductor component according to claim 17, wherein said dielectric is provided with openings through which said power components are contactable.
19. (Previously presented) A semiconductor component according to claim 10 comprising:
at least one second vertical power component extending from said front side to said back side of said silicon substrate, separated from said first vertical power component by a second trench filled with an insulation, said second trench extending from said front side to said back side of said silicon substrate,
wherein said insulation comprises at least partly one dielectric and
wherein said at least one second vertical power component is designed approximately ring-shaped and/or disk-shaped and is arranged eccentrically or concentrically around said common point of reference on said silicon substrate.
20. (New) A semiconductor component comprising:

at least one first vertical power component extending from a front side to a back side of a silicon substrate;

at least one lateral, active component between which at least one trench filled with an insulation is placed, said at least one trench extending from said front side to said back side of said silicon substrate,

wherein said at least one vertical power component and said at least one lateral, active component are designed approximately ring-shaped and/or disk-shaped and are arranged eccentrically or concentrically around a common point of reference on said silicon substrate; and

at least one second vertical power component extending from said front side to said back side of said silicon substrate, separated from said first vertical power component by a second trench filled with an insulation, said second trench extending from said front side to said back side of said silicon substrate,

wherein said insulation comprises at least partly one dielectric, and

wherein said at least one second vertical power component is designed approximately ring-shaped and/or disk-shaped and is arranged eccentrically or concentrically around said common point of reference on said silicon substrate.